

CLIPPEDIMAGE= JP405102336A

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TITLE: SEMICONDUCTOR DEVICE

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INVENTOR-INFORMATION:

NAME

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INT-CL (IPC): H01L023/12;H01L025/04 ;H01L025/18

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ABSTRACT:

PURPOSE: To obtain a semiconductor device wherein its integration density is high, its performance is high and its reliability is high.

CONSTITUTION: The title semiconductor device is featured in the following manner: a plurality of insulating substrates 12 to 15 are laminated; conductive sheets 18 are installed inside cavities 20 whose side face is step-shaped; semiconductor chips 16 are bonded to the conductive sheets 18 and to the first-layer insulating substrate 12; and via holes 21 are made in a multilayer insulating substrate. Thereby, it is possible to realize the semiconductor

device in which the integration density of the semiconductor chips is enhanced, in which an arbitrary potential can be applied to the semiconductor chips via the via holes and whose performance and reliability are high.

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